

Integrated bypass diode for Solar cell Module

Features

- Schotty Barrier hight diode;
- Low thermal resistance;
- Lower forward voltage drop, low power loss;
- Isolate Package design, ideal for heat dispersion;
- High forward current capability;
- Excellent anti-humidity;
- Low profile package;
- High forward surge capability;

Mechanical Data

- Case: GFM;
- Terminals: Copper;
- High temperature soldering guaranteed; Heated-tool welding 260 °C,10 seconds
- Marking: As marked on product;

Order Information

Package	GFM	
PVC tube	30pcs/ tube	
Inner Box	300pcs/ Inner box	
Carton	1500pcs/ Carton	

Typical Applications

For the protection of solar cell bypass box. Using DC forward current without reverse bias.

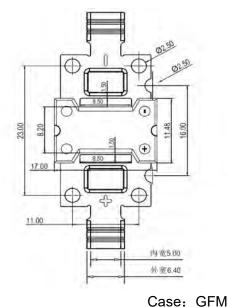
Maximum Ratings and Electrical Characteristics

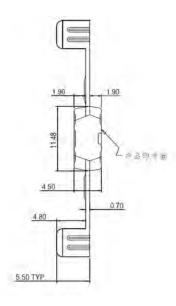
Ratings at 25 $\!\!\!^{\,\circ}\!\!\!^{\,\circ}$ ambient temperature unless otherwise specified.





RoHS COMPLIANT





Dimensions in milimeters

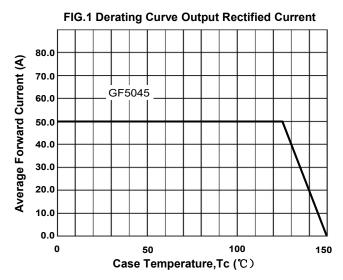
For capacitive load, derate current by 20%.				
Parameter		Symbol	GF5045	Unit
Maximum repetitive peak reverse voltage		V _{RRM}	45	Volt
Maximum working peak reverse voltage		V _{RWM}	45	Volt
Average rectified output current @ 60Hz sine wave, Ta=25℃		Io	50	Amps
Non-Repetitive Peak forward surge current @ 60Hz, single sine-wave load		I _{FSM}	450	Amps
Rating for fusing (t<8.3ms)		l ² t	840	A ² sec
Instantaneous forward voltage drop	@IF=10A @IF=20A @IF=30A @IF=50A	V _F	0.39 Typ. 0.44 max. 0.43 Typ. 0.48 max. 0.46 Typ. 0.51 max. 0.49 Typ. 0.54 max.	Volt
Reverse Current at Rated DC reverse Voltage	@Tj=25℃	I _R	180 Typ. 500 max.	μΑ
	@Tj=125 ℃	I _R	80.00 Typ. 150.00 max.	mA
Typical capacitance (1.0 MHz and Applied reverse Voltage of 5.0V D.C)		C _j	2600	pF
Typical thermal resistance		R _{OJ-c}	1.5	°C/W
Storage Temperature		T _{STG}	-55 to +150	°C
Junction Temperature IN DC Forward Mode, without reverse bias, t ≤1 h		TJ	-55 to +150	င

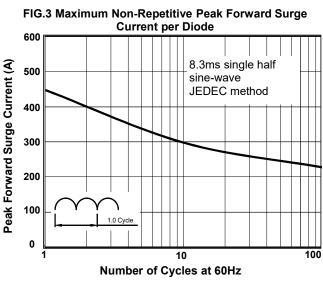
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Ratings and Characteristics Curves

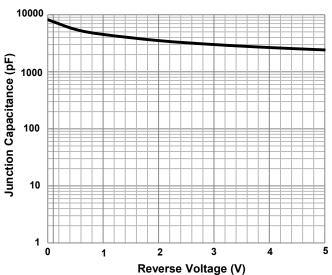
(TA = 25℃ unless otherwise noted)





Number of Cycles at 60Hz

FIG.5 Typical Junction Capacitance per Diode



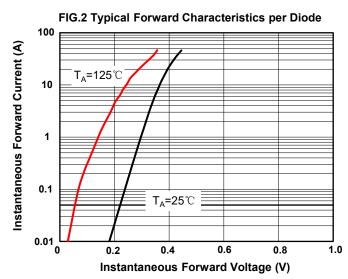
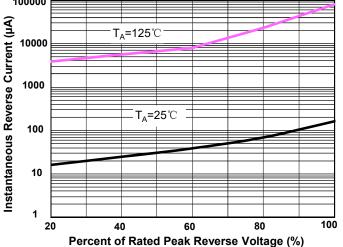


FIG.4 Typical Reverse Characteristics per Diode



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